

Title (en)

FORMING A PLANAR SURFACE OVER A SUBSTRATE BY MODIFYING THE TOPOGRAPHY OF THE SUBSTRATE

Title (de)

FORMEN EINER EBENEN OBERFLÄCHE ÜBER EINEM SUBSTRAT DURCH MODIFIZIERUNG DER TOPOGRAPHIE DES SUBSTRATS

Title (fr)

FORMATION D'UNE SURFACE PLANE SUR UN SUBSTRAT PAR MODIFICATION DE SA TOPOGRAPHIE

Publication

EP 0791227 A4 19980401 (EN)

Application

EP 95940684 A 19951113

Priority

- US 9514681 W 19951113
- US 33700094 A 19941110

Abstract (en)

[origin: WO9615552A1] A method of forming a substantially planar surface over a trench isolation region (33) of a semiconductor substrate (30). Latent active regions (42) are formed within the trench isolation region (33). A dielectric layer (38) is then deposited over the surface of the semiconductor substrate (30). Then, the dielectric layer (38) is polished back to form a planar surface.

IPC 1-7

H01L 23/053; **H01L 23/12**; **H01L 23/48**; **H01L 23/52**; **H01L 21/76**; **H01L 21/48**

IPC 8 full level

B26F 3/02 (2006.01); **B26D 7/08** (2006.01); **B26F 3/00** (2006.01); **B65C 9/18** (2006.01); **B65H 35/07** (2006.01); **B65H 35/10** (2006.01); **H01L 21/304** (2006.01); **H01L 21/76** (2006.01); **H01L 21/762** (2006.01); **H01L 23/14** (2006.01)

CPC (source: EP KR)

B26D 7/088 (2013.01 - EP); **B26F 3/002** (2013.01 - EP); **B65C 9/1896** (2013.01 - EP); **B65H 35/10** (2013.01 - EP); **H01L 21/76229** (2013.01 - EP); **H01L 23/053** (2013.01 - KR); **H01L 23/12** (2013.01 - KR)

Citation (search report)

- [XY] EP 0545263 A2 19930609 - SONY CORP [JP]
- [Y] US 5278105 A 19940111 - EDEN SHMUEL [IL], et al
- [A] PATENT ABSTRACTS OF JAPAN vol. 015, no. 254 (E - 1083) 27 June 1991 (1991-06-27)
- [A] PATENT ABSTRACTS OF JAPAN vol. 018, no. 024 (P - 1675) 14 January 1994 (1994-01-14)
- [A] PATENT ABSTRACTS OF JAPAN vol. 012, no. 328 (E - 654) 6 September 1988 (1988-09-06)
- See references of WO 9615552A1

Designated contracting state (EPC)

DE FR GB IT

DOCDB simple family (publication)

WO 9615552 A1 19960523; AU 4235196 A 19960606; CN 1171166 A 19980121; EP 0791227 A1 19970827; EP 0791227 A4 19980401; JP H10512098 A 19981117; KR 970707582 A 19971201; TW 299458 B 19970301

DOCDB simple family (application)

US 9514681 W 19951113; AU 4235196 A 19951113; CN 95197102 A 19951113; EP 95940684 A 19951113; JP 51623496 A 19951113; KR 19970703143 A 19970510; TW 84111123 A 19951020